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**April 2013** 

# FDT3N40

# N-Channel UniFET<sup>™</sup> MOSFET 400 V, 2.0 A, 3.4

### **Features**

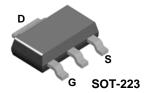
- $R_{DS(on)} = 3.4 \Omega \text{ (Max.)} @ V_{GS} = 10 \text{ V}, I_D = 1.0 \text{ A}$
- Low Gate Charge (Typ. 4.5 nC)
- Low Crss (Typ. 3.7 pF)
- 100% Avalanche Tested

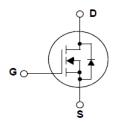
# **Applications**

- LCD/LED TV
- Lighting
- Uninterruptible Power Supply

# **Description**

UniFET™ MOSFET is Fairchild Semiconductor®'s high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





# **Absolute Maximum Ratings**

Symbol	Parameter			FDT3N40	Unit
V <sub>DSS</sub>	Drain-Source Voltage			400	V
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25 - Continuous (T <sub>C</sub> = 10		2.0 * 1.2 *	A A
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	8.0 *	А
V <sub>GSS</sub>	Gate-Source voltage			±30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy		(Note 2)	46	mJ
I <sub>AR</sub>	Avalanche Current		(Note 1) 2		A
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	0.2	mJ
dv/dt	Peak Diode Recover	y dv/dt	(Note 3)	4.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C			2 0.02	W W/°C
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		urpose,	300	°C

<sup>\*</sup> Drain current limited by maximum junction temperature

# Thermal Characteristics

Symbol	Parameter	FDT3N40	Unit
$R_{ heta JA}^{ *}$	Thermal Resistance, Case-to-Sink Typ.	60	°C/W

<sup>\*</sup> Surface Mounted on JESD51-3 Board, T<0.1sec.

# **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Reel Size	Tape Width	Quantity
FDT3N40	FDT3N40TF	SOT-223	330mm	12mm	4000

# **Electrical Characteristics** $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit		
Off Charac	Off Characteristics							
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	400			V		
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C		0.4		V/°C		
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 400V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 320V, T <sub>C</sub> = 125°C			1 10	μA μA		
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V			100	nA		
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS} = -30V$ , $V_{DS} = 0V$			-100	nA		
On Charac	On Characteristics							
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V		
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 1A		2.8	3.4	Ω		
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 40V$ , $I_D = 1A$ (Note 4)		2		S		
Dynamic C	Dynamic Characteristics							
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V,		173	225	pF		
C <sub>oss</sub>	Output Capacitance	f = 1.0MHz		30	40	pF		
C <sub>rss</sub>	Reverse Transfer Capacitance			3.7	6	pF		
Switching	Characteristics							
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 200V, I_{D} = 2A$		10	30	ns		
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25\Omega$		30	70	ns		
t <sub>d(off)</sub>	Turn-Off Delay Time			10	30	ns		
t <sub>f</sub>	Turn-Off Fall Time	(Note 4, 5)		25	60	ns		
Qg	Total Gate Charge	V <sub>DS</sub> = 320V, I <sub>D</sub> = 2A		4.5	6	nC		
$Q_{gs}$	Gate-Source Charge	V <sub>GS</sub> = 10V		1.2		nC		
$Q_{gd}$	Gate-Drain Charge	(Note 4, 5)		2		nC		
Drain-Source Diode Characteristics and Maximum Ratings								
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				2	Α		
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				8	Α		
$V_{SD}$	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 2A			1.4	V		
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0V$ , $I_S = 2A$		210		ns		
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s   (Note 4)$		0.75		μС		

#### NOTES

<sup>1.</sup> Repetitive Rating: Pulse width limited by maximum junction temperature

<sup>2.</sup> L = 10mH, I  $_{AS}$  = 2A, V  $_{DD}$  = 50V, R  $_{G}$  = 25 $\Omega$ , Starting T  $_{J}$  = 25°C

<sup>3.</sup> I\_{SD}  $\leq$  2A, di/dt  $\leq$  200A/µs, V\_{DD}  $\leq$  BV\_DSS, Starting T\_J = 25°C

<sup>4.</sup> Pulse Test: Pulse width  $\leq 300 \mu \text{s}, \ \text{Duty Cycle} \leq 2\%$ 

 $<sup>{\</sup>bf 5.} \ {\bf Essentially} \ {\bf Independent} \ {\bf of} \ {\bf Operating} \ {\bf Temperature} \ {\bf Typical} \ {\bf Characteristics}$ 

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

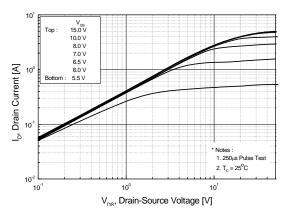


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

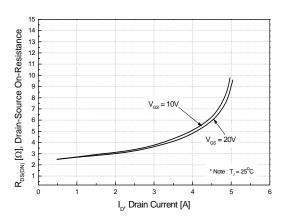


Figure 5. Capacitance Characteristics

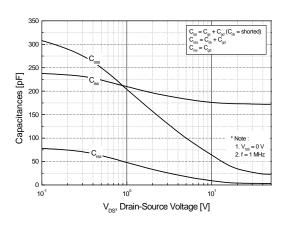


Figure 2. Transfer Characteristics

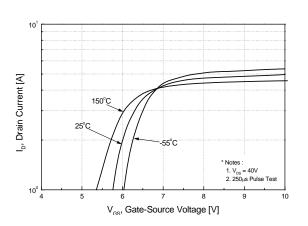
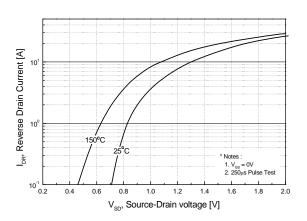
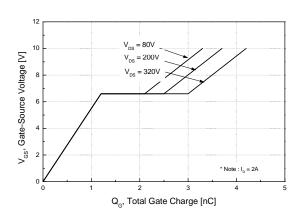


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue



**Figure 6. Gate Charge Characteristics** 



# **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

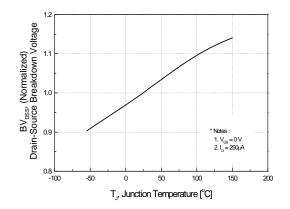


Figure 8. On-Resistance Variation vs. Temperature

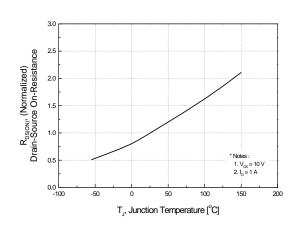
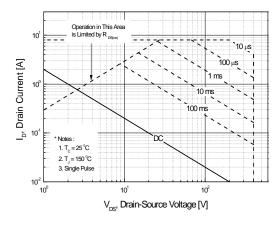


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature



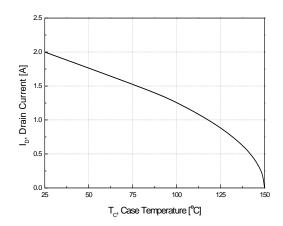
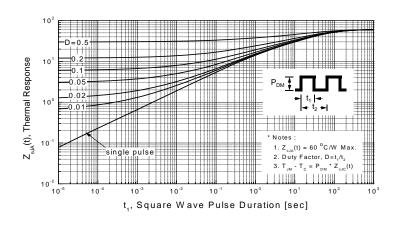
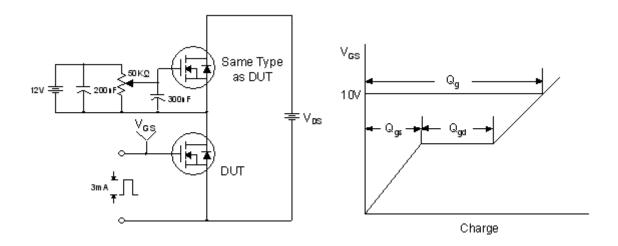


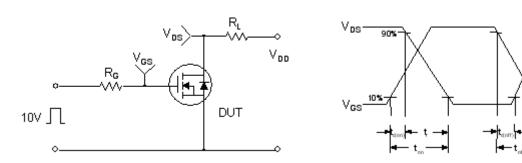
Figure 11. Transient Thermal Response Curve



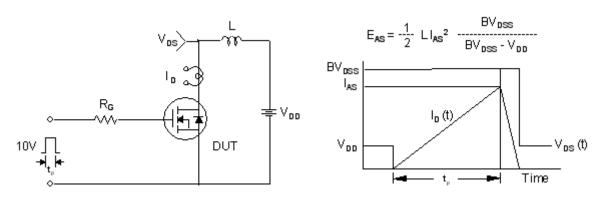
# **Gate Charge Test Circuit & Waveform**



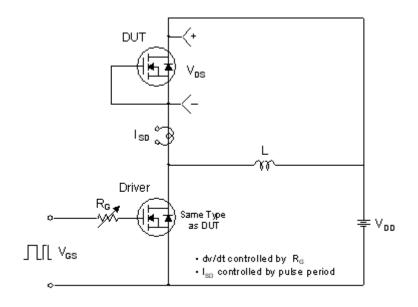
# **Resistive Switching Test Circuit & Waveforms**

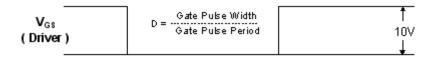


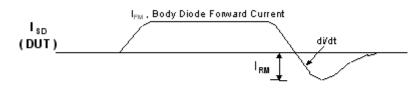
# **Unclamped Inductive Switching Test Circuit & Waveforms**

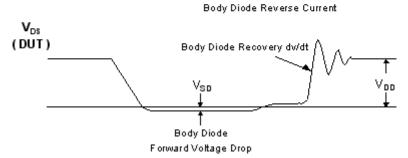


# Peak Diode Recovery dv/dt Test Circuit & Waveforms



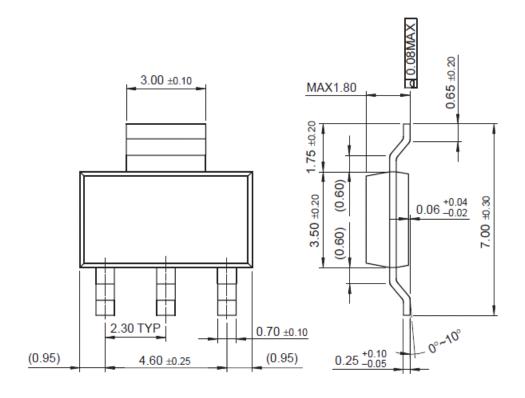


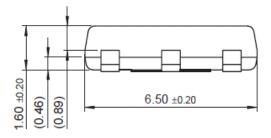




# **Mechanical Dimensions**

# SOT-223









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